

SPTS Claritas – Enhanced OES

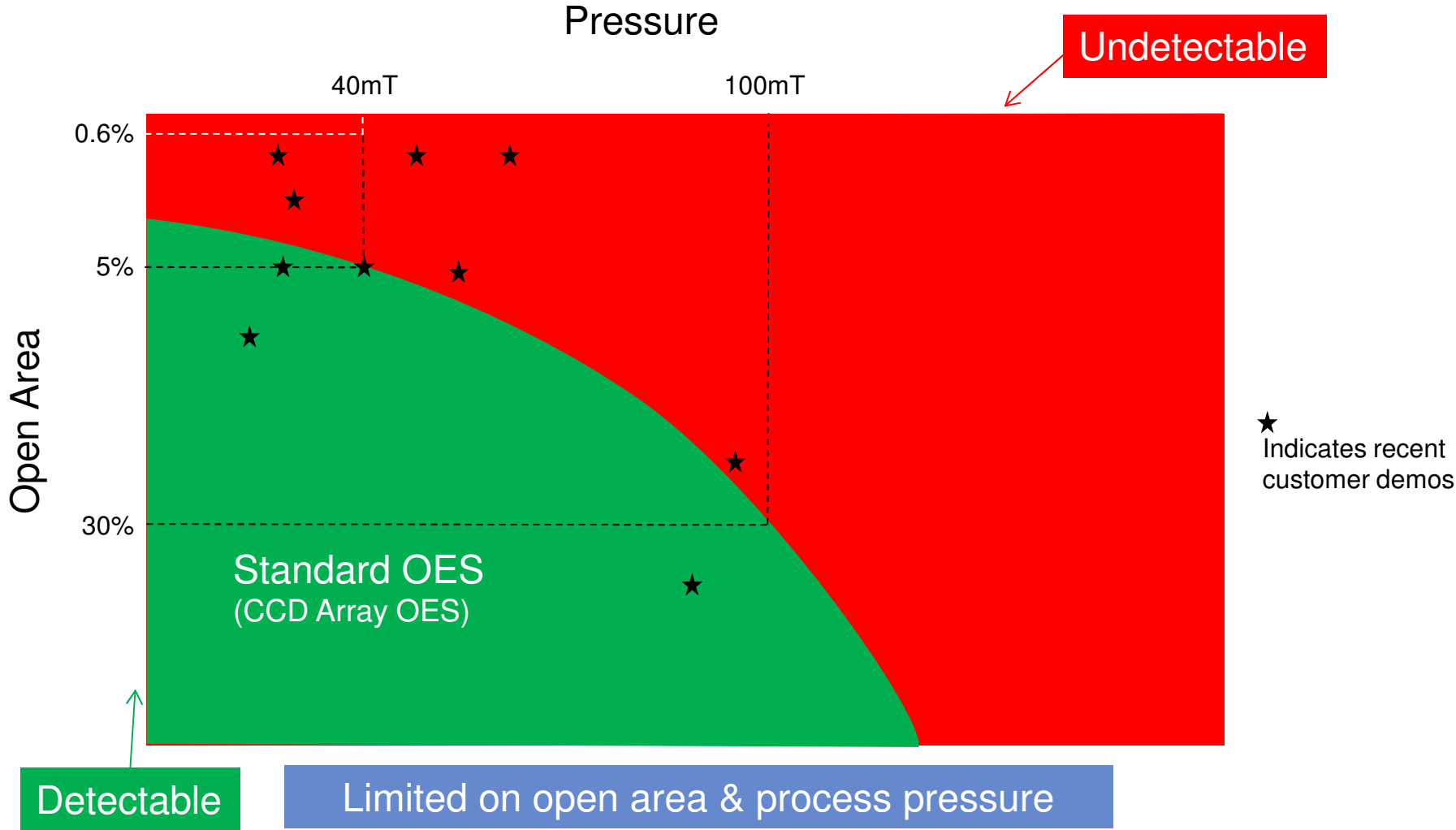
February 2012



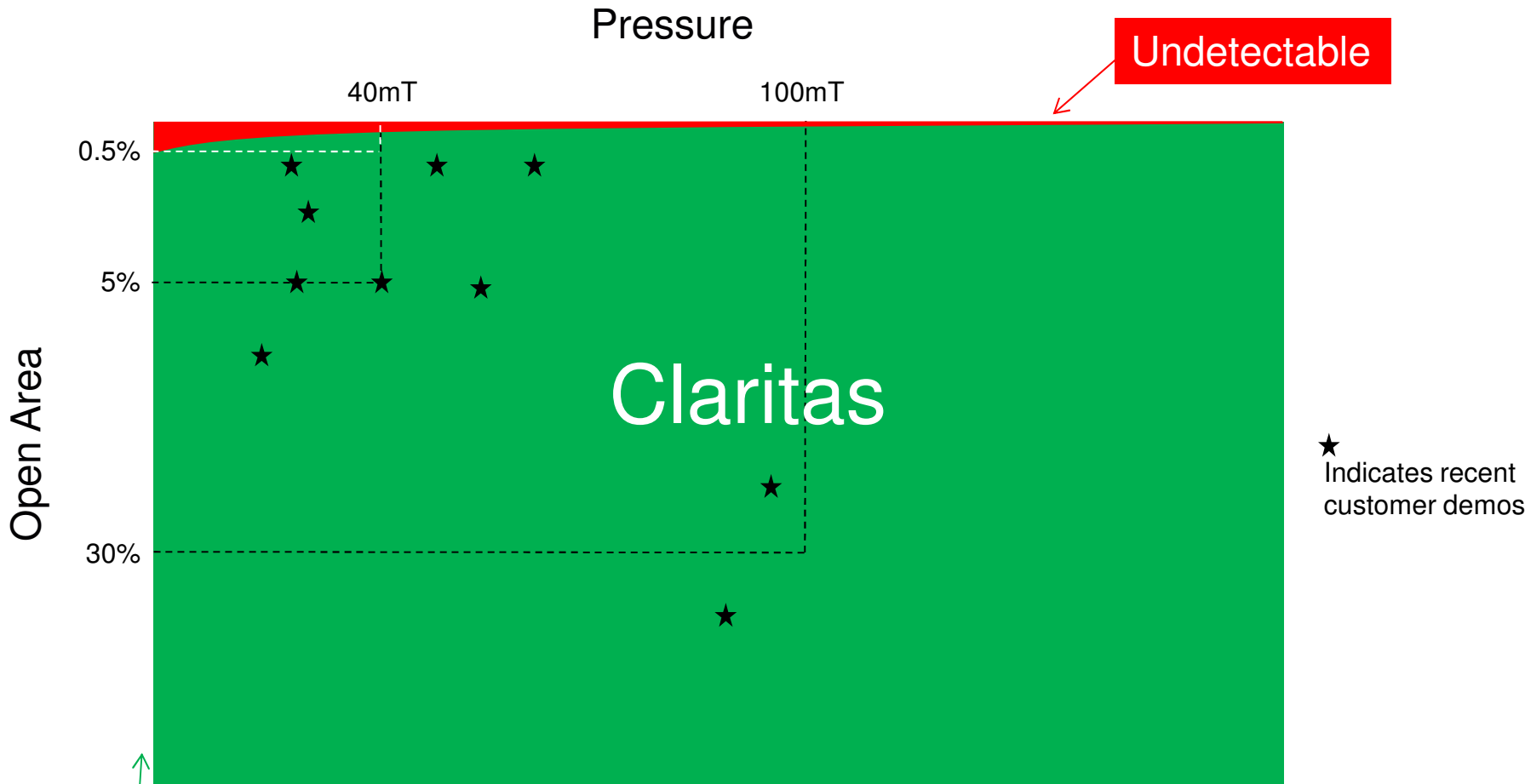
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- Historically it has only been possible to end-point a subset of the deep Si etches that MEMS & TSV customers require for their production
- Until now no Etch vendor has been able to successfully end-point ..
 - Wafers that have very low exposed areas (0.1-3.0% open area)
 - High pressure processes that operate in the 100 mtorr range
- Claritas is the first end-point system to address these process regimes
- Claritas extends the use of existing OES options available on SPTS DRIE modules and enhances the detection of reactants and/or by-products
- Claritas is operated under fully automatic recipe control

Standard OES End-Point



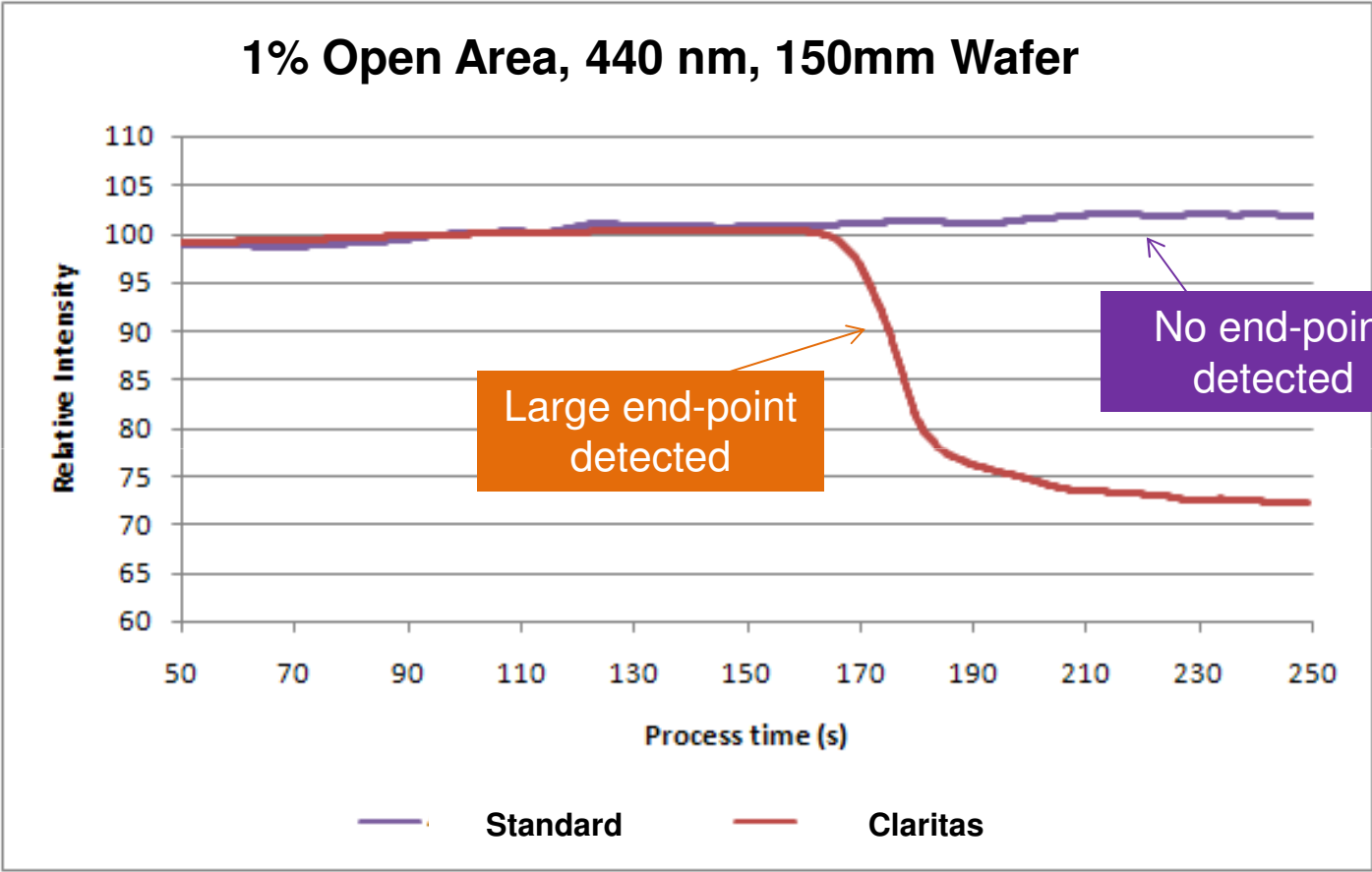
Claritas – Advanced End-Point



Detectable

Large operating envelope
Successful end-pointing within previously
inaccessible process regimes

Claritas Tests at SPTS

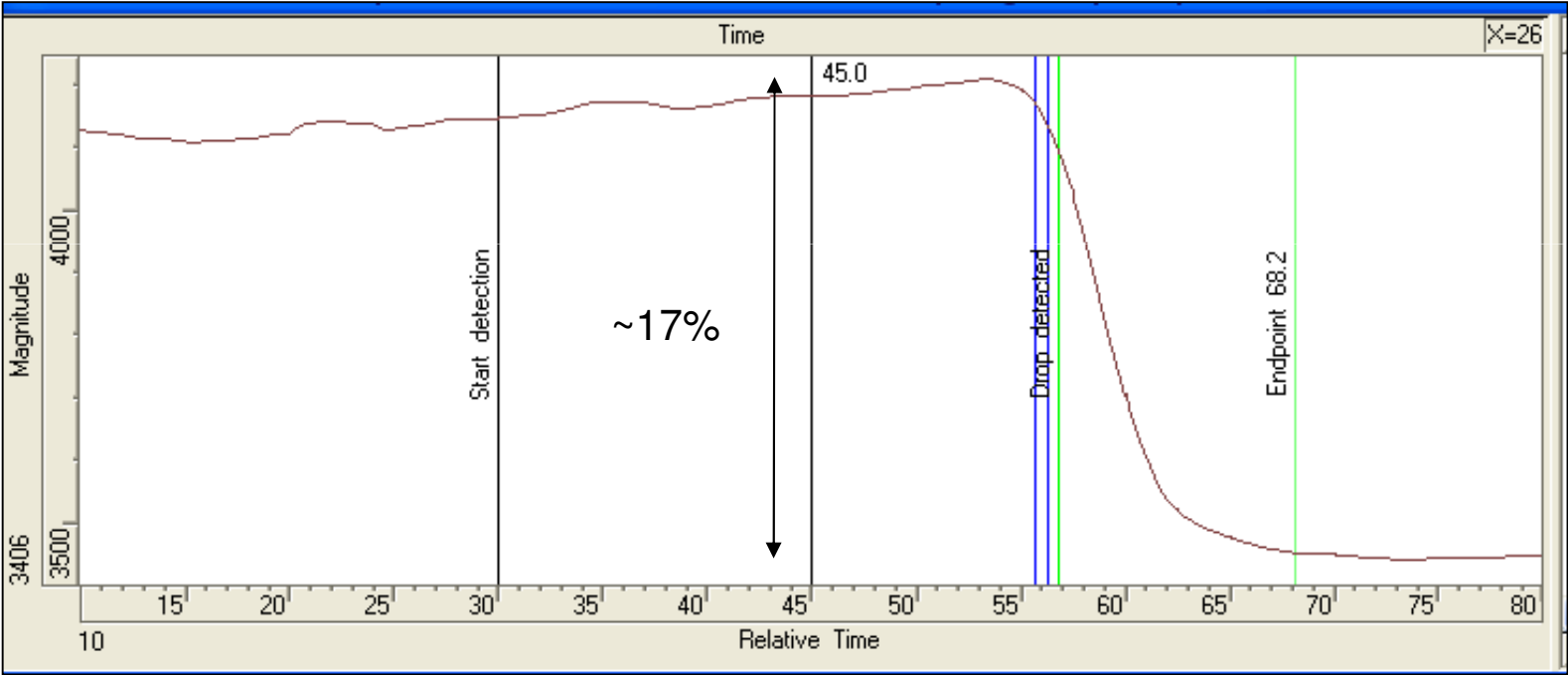


Claritas easily copes with 1% open area

Claritas Tests at SPTS



- Customer recipe – customer #1
- 150 mm wafer, <1% open area

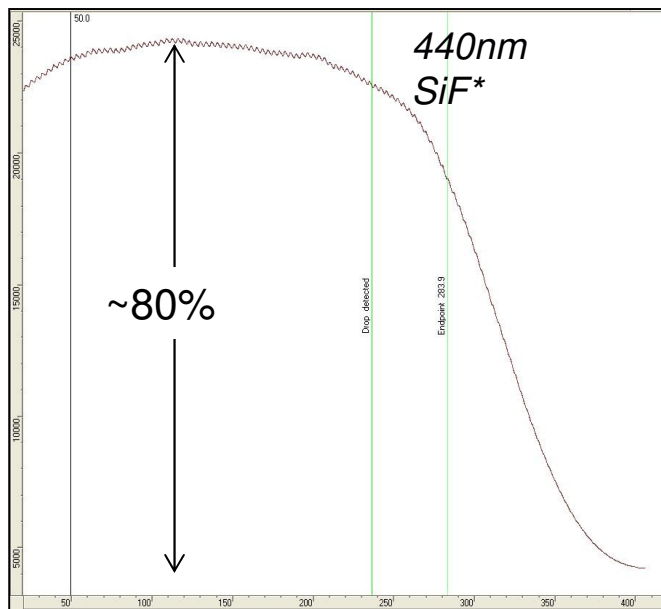


Claritas easily copes with <1% open area

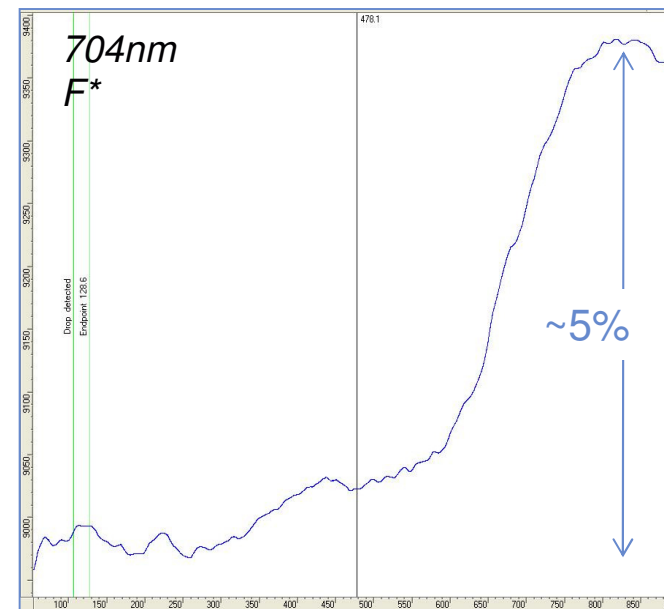
Claritas Tests at SPTS



- Customer recipe – customer #2
- 150 mm wafer, Application #1, ~50% open area
- Best endpoints available for a given recipe condition



Claritas

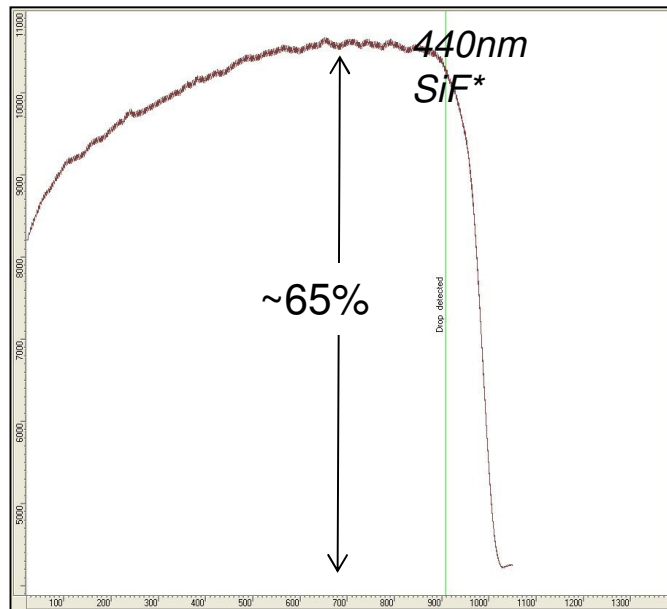


Standard
OES

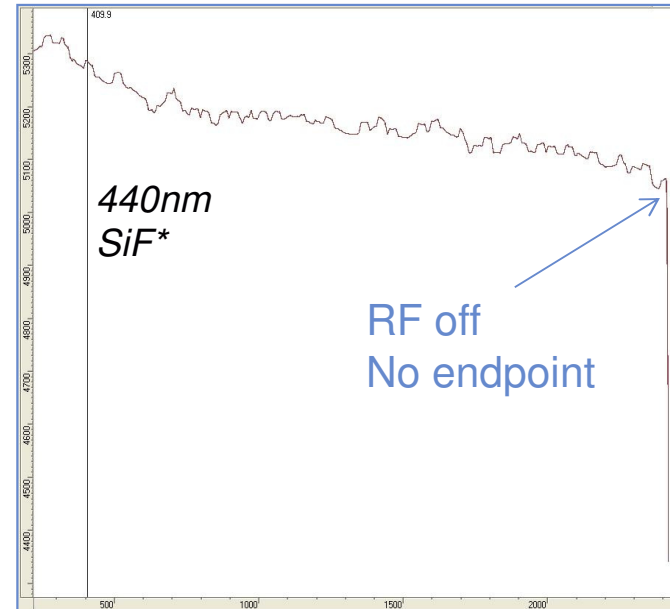
Claritas Tests at SPTS



- Customer recipe – customer #2
- 150 mm wafer, Application #2, ~30% open area
- Best endpoints available for a given recipe condition



Claritas

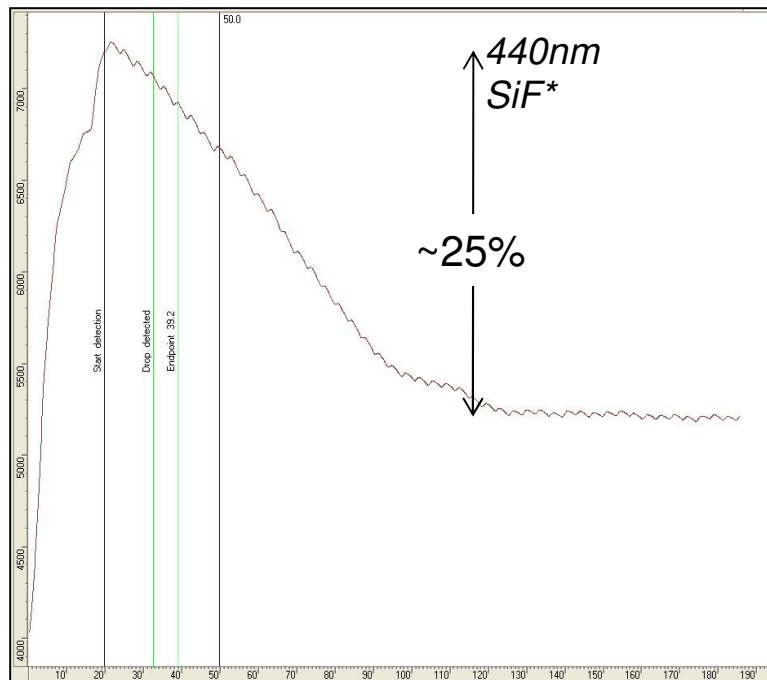


Standard OES

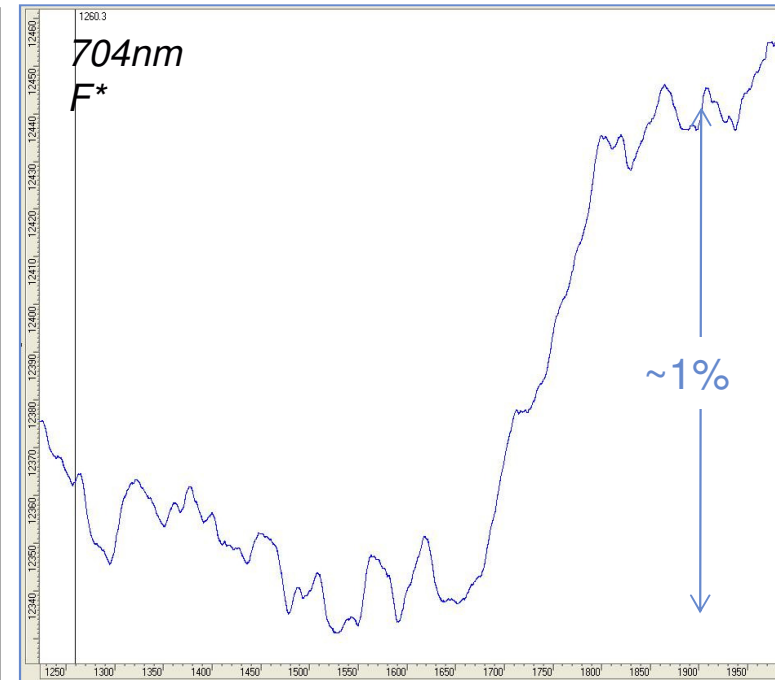
Claritas Tests at SPTS



- Customer recipe – customer #3
- 150 mm wafer, Application #1, 16% open area
- Best endpoints available for a given recipe condition



Claritas

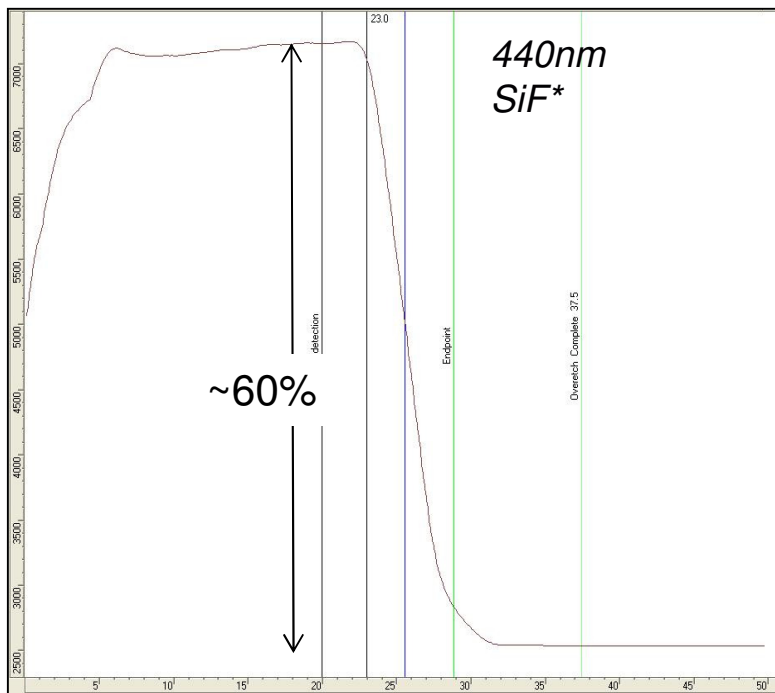


Standard OES

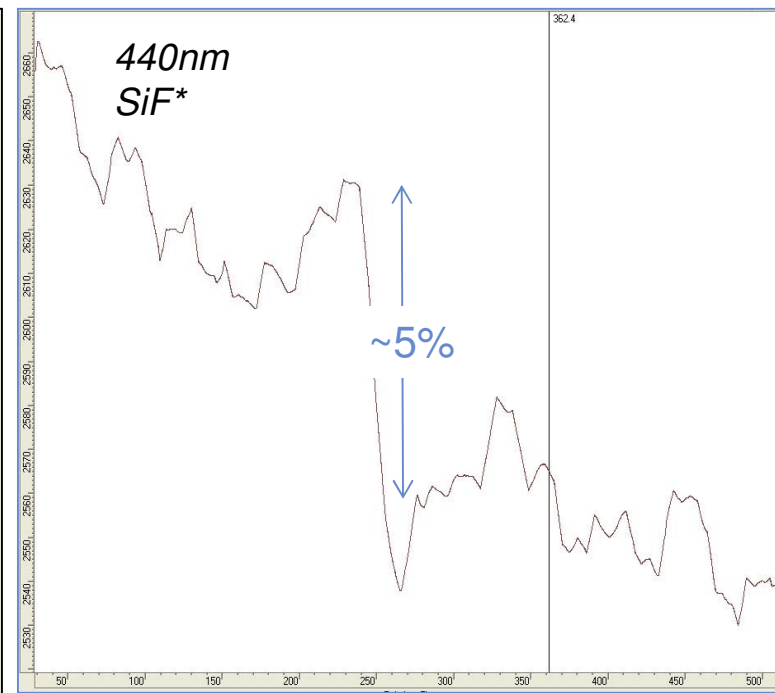
Claritas Tests at SPTS



- Customer recipe – customer #3
- 150 mm wafer, Application #2, ~20% open area
- Best endpoints available for a given recipe condition



Claritas

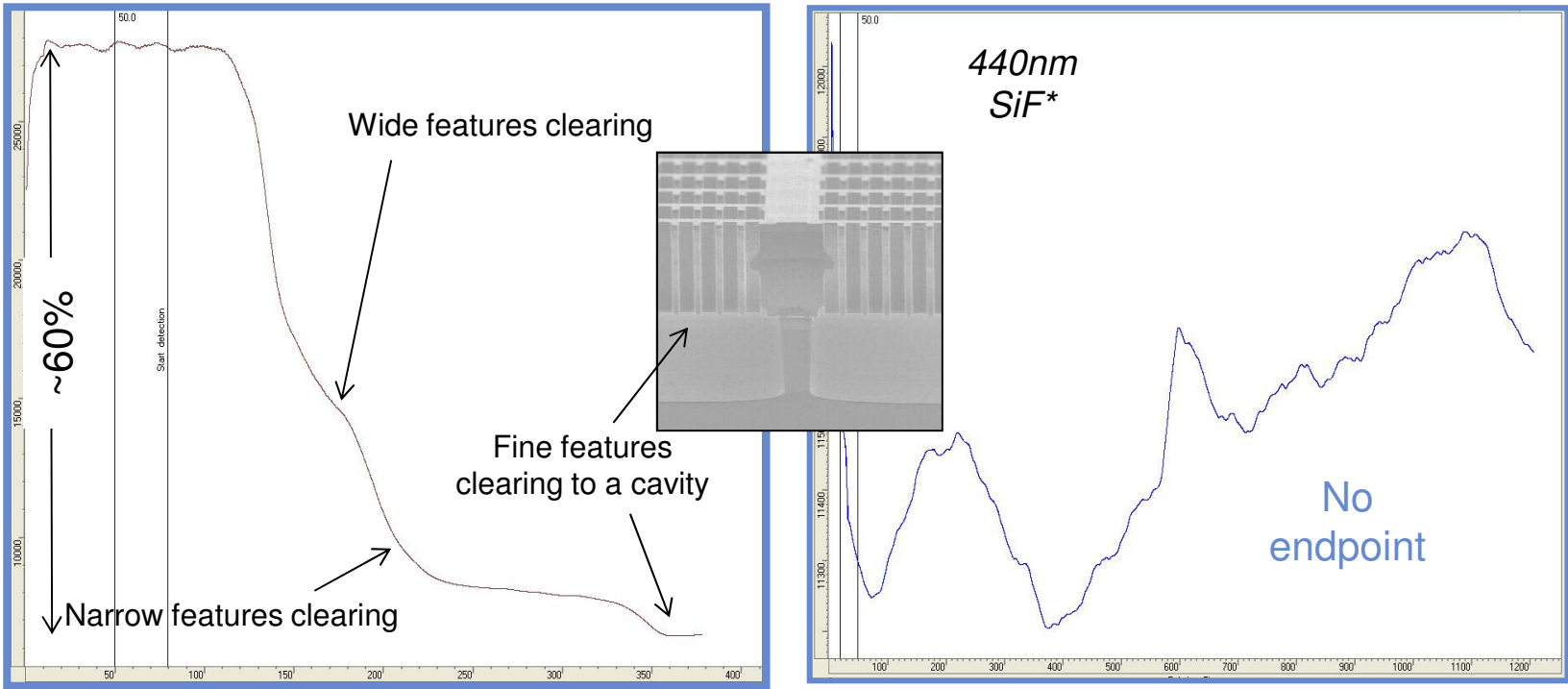


Standard OES

Claritas Tests at SPTS



- Customer recipe – customer #3
- 150 mm wafer, Application #3, ~20% open area
- 3 Discrete endpoints seen for multiple features on same mask



Claritas

Standard OES

Claritas Performance Summary



Wafers	Open area	Process	Standard OES Signal Change	Claritas Signal Change
Internal	~1%	SPTS'	None	28%
Customer #1	<1%	Customer's	None	17%
Customer #2	~50%	Customer's Application #1	5%	80%
	~30%	Customer's Application #2	None	65%
Customer #3	~16%	Customer's Application #1	1%	25%
	~20%	Customer's Application #2	5%	60%
	~20%	Customer's Application #3	None	60%

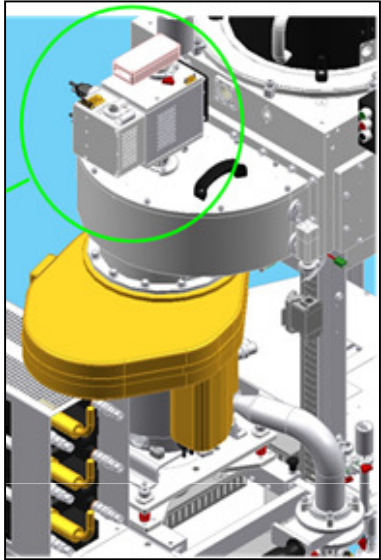
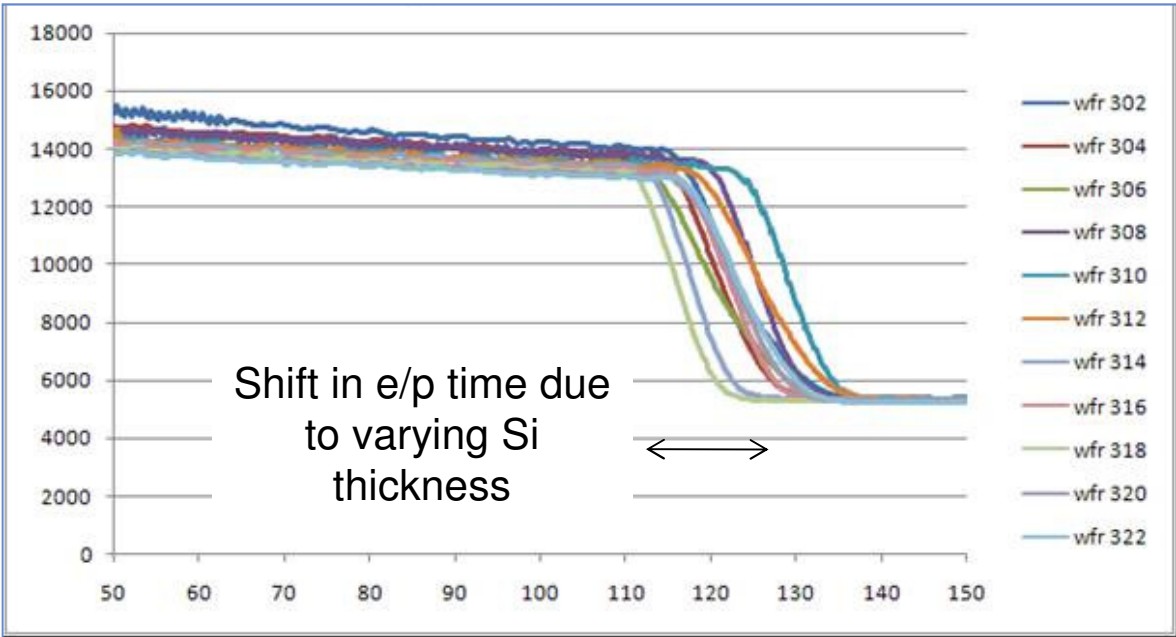
Claritas delivers:

- Large operating envelope
- Successful end-pointing across all applications

Claritas – Additional Example



- 70 x 70 μm TSV etch stopping on oxide
- Objective
 - Consistent, reliable end-pointing



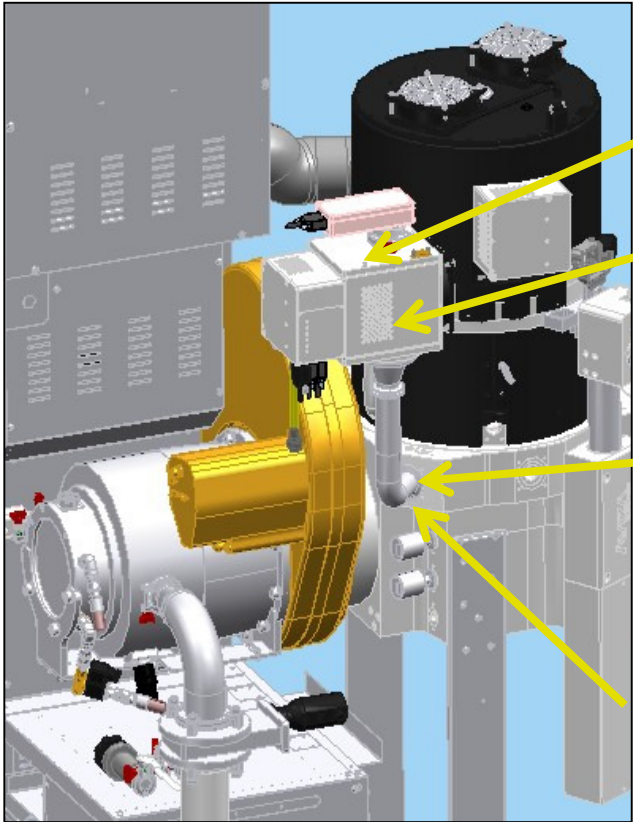
Objective met:
Good e/p reliability
~60% signal change
Allows early capture of e/p to improve wafer repeatability

Installation

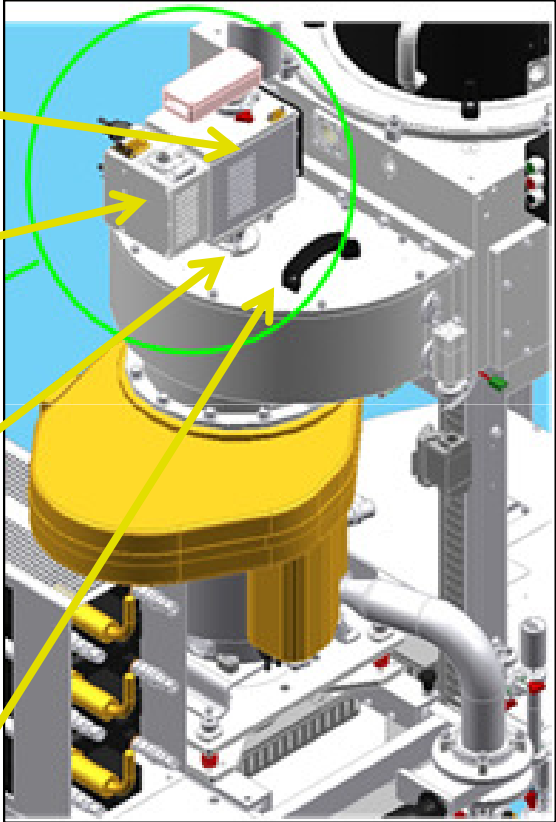
(Pegasus DSi, Pegasus Rapier)



200 mm Module



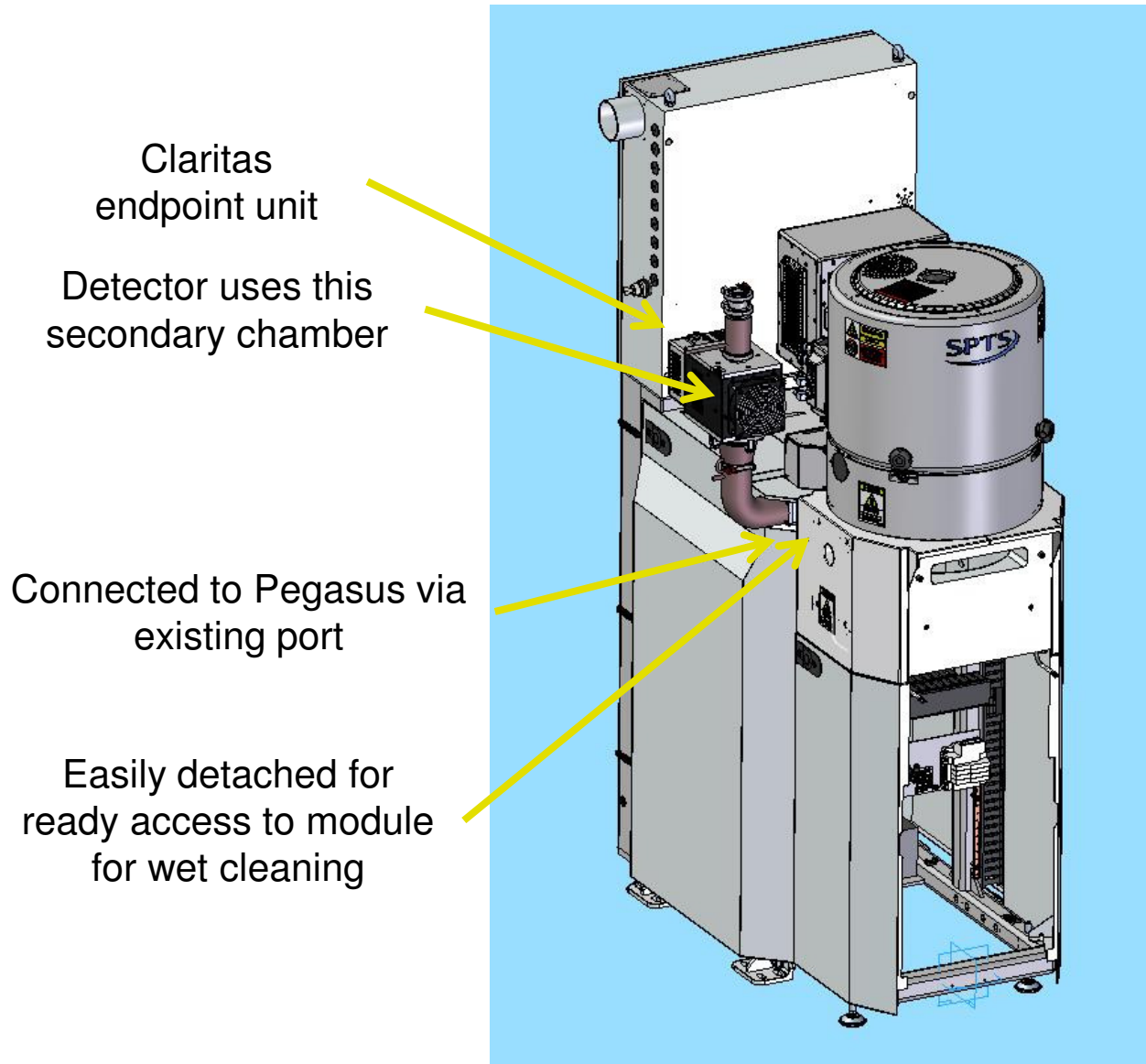
300 mm Module



- Claritas endpoint unit
- Detector uses this secondary chamber
- Connected to PM via existing port
- Easily detached for ready access to module for wet cleaning

Claritas easily retrofitted
Claritas is compatible with existing
OES detectors

Installation (Pegasus)



Claritas easily retrofitted

Claritas is compatible with existing OES detectors

Return on Investment



- ROI calculations have been completed
- Based on 3 deep Si etch applications
 - Combination of TSV & MEMS etches
- Assume periodic wafer cleaving (for SEM inspection) is required when no endpoint system is used
 - Varied between 1 per lot, 1 per day, 1 per shift and 1 per week
 - Assume periodic cleaving reduces to 1 per week when Claritas is used
 - Assume 0.1% wafer scrap when Claritas is not used
- ROI period is calculated based on the combined costs of testing wafers and the risk of a low level (0.1%) of wafer scrap
 - These calculations are available on request

ROI calculated to be 1-3 months depending on whether the customer already has a CCD OES

- Claritas is the first end-point system to work successfully in the low exposed area (<1.0-3.0%) & high pressure (~100 mtorr) process regimes that are required for MEMS & TSV etching

- Claritas is compatible with & greatly extends the reach of SPTS's existing OES options

- Available for....
 - Pegasus DSi
 - Pegasus Rapier
 - Pegasus (PRO2 models only)